

09/750,116
WAK.071

REMARKS

Claims 1-23 are all the claims presently pending in the application. Claims 2, 4-13 and 16-23 have been amended to more particularly define the invention. Attached hereto is a marked-up version of the changes made to the specification and claims by the current Amendment.

It is noted that the claim amendments are made only for more particularly pointing out the invention, and not for distinguishing the invention over the prior art, narrowing the claims or for any statutory requirements of patentability. Further, Applicant specifically states that no amendment to any claim herein should be construed as a disclaimer of any interest in or right to an equivalent of any element or feature of the amended claim.

✓ Applicant gratefully acknowledges the Examiner's statement that all of the claims are now allowable. Submitted herewith are copies of the international application PCT/JP99/03580 from which the present Application claims priority, and an English translation of the international application as requested by the Examiner in order to comply with MPEP §1895.

In view of the foregoing, Applicant submits that claims 1-²³, all the claims presently pending in the application, are patentably distinct over the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

09/750,116
WAK.071

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Attorney's Deposit Account No. 50-0481.

Respectfully Submitted,

Date: 3/31/09



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09/750,116
WAK.071

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

Please amend the Specification to read as follows:

On page 1, line 1, before "TECHNICAL FIELD" please insert:

This is a continuation of International Application PCT/JP99/03580, which has an international filing date of July 2, 1999, was not published in English under PCT Article 21(2), and is now abandoned.

IN THE CLAIMS:

Please amend the claims to read as follows:

2. (Amended) A polymer which is obtained by polymerizing the (meth) acrylate derivative according to [described in] claim 1, or copolymerizing the (meth) acrylate derivative according to [described in] claim 1 with another polymerizable compound.

4. (Amended) A photoresist material comprising: [which includes at least]
the polymer according to [described in] claim 2; and
a photo-acid generator for generating an acid by exposure.

5. (Amended) A photoresist material comprising: [which includes at least]
the polymer according to [described in] claim 3; and
a photo-acid generator for generating an acid by exposure.

6. (Amended) A photoresist material according to claim 4, [which] further comprising:
[includes]
a polyhydric alcohol.

7. (Amended) A photoresist material according to claim 5, [which] further comprising:
[includes]

09/750,116
WAK.071

a polyhydric alcohol.

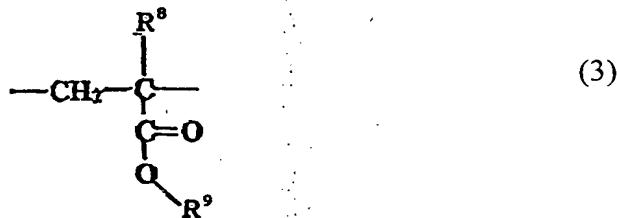
8. (Amended) A photoresist composition, comprising: [which comprises] 70 to 99.8% by weight of the polymer according to [described in] claim 2; and 0.2 to 30% by weight of a photo-acid generator for generating an acid by exposure.
9. (Amended) A photoresist composition, comprising: [which comprises] 70 to 99.8% by weight of the polymer according to [described in] claim 3; and 0.2 to 30% by weight of a photo-acid generator for generating an acid by exposure.
10. (Amended) A method for forming a pattern, comprising: [which comprises a step of] applying the photoresist material according to [described in] claim 4 onto a substrate to be worked; [, a step of]
exposing the material to a light having a wavelength of 180 to 220 nm; [, a step of carrying out]
baking said material; [,] and [a step of]
selectively dissolving one of an exposed portion and an unexposed portion of said material to develop said pattern [performing development].
11. (Amended) A method for forming a pattern, comprising: [which comprises a step of] applying the photoresist material according to [described in] claim 5 onto a substrate to be worked; [, a step of]
exposing the material to a light having a wavelength of 180 to 220 nm; [, a step of]
baking said material; [,] and [a step of]
selectively dissolving one of an exposed portion and an unexposed portion of said material to develop said pattern [performing development].
12. (Amended) The method for forming the pattern according to claim 10 wherein said [the exposure] light comprises [is] an ArF excimer laser light.

09/750,116
WAK.071

13. (Amended) The method for forming the pattern according to claim 11 wherein said [the exposure] light comprises [is] an ArF excimer laser light.

16. (Amended) A polymer which is obtained by polymerizing the (meth) acrylate derivative according to [described in] claim 15, or copolymerizing the (meth) acrylate derivative according to [described in] claim 15 with another polymerizable compound and has a weight-average molecular weight of 2000 to 200000.

17. (Amended) A [In a] resin for resist having a [, the] solubility to an alkaline aqueous solution [of] which increases due to the decomposition of an acid-decomposable group thereof by an action of an acid, said resin comprising [is the resin for resist having] a (meth)acrylate unit of an alicyclic lactone structure represented by the formula (3):



wherein R⁸ is a hydrogen atom or a methyl group, and R⁹ is a hydrocarbon group of 7 to 16 carbon atoms having an alicyclic lactone structure.

18. (Amended) The resin for resist according to claim 17, wherein said resin comprises [is] the polymer according to one of claim 2 or claim 14.

19. (Amended) A photoresist material comprising: [which includes at least] the polymer according to one of claims [described in claim] 14 or 16; and

09/750,116
WAK.071

a photo-acid generator for generating an acid by exposure.

20. (Amended) The photoresist material according to claim 19, [which] further comprising: [includes]

a polyhydric alcohol.

21. (Amended) A photoresist composition comprising: [which at least comprises] 70 to 99.8% by weight of the polymer according to one of claims [described in claim] 17 or 18; and

0.2 to 30% by weight of a photoacid generator for generating an acid by exposure.

22. (Amended) A method for forming a pattern comprising: [which comprises at least a step of]

applying the photoresist composition according to [described in] claim 21 onto a substrate to be worked; [, a step of]

exposing the composition to a light having a wavelength of 180 to 220 nm; [, a step of]

baking said material; [,] and [a step of]

selectively dissolving one of an exposed portion and an unexposed portion of said material to develop said pattern [performing development].

23. (Amended) The method for forming the pattern according to claim 22, wherein said [the exposure] light comprises [is] an ArF excimer laser light.